

PULSED WRITE TECHNIQUES FOR MAGNETO-RESISTIVE MEMORIES

Abstract of the Disclosure

A magneto-resistive memory that has a shared word line and sense line is disclosed. By providing the shared word line and sense line, the number of relatively large drivers required to drive the word line and sense line currents can be reduced. This reduces the peripheral overhead of the memory, and may increase the overall density and reduce the overall power of the memory.

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